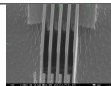
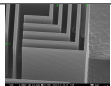
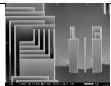

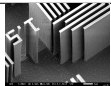
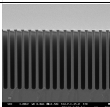
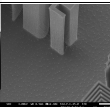
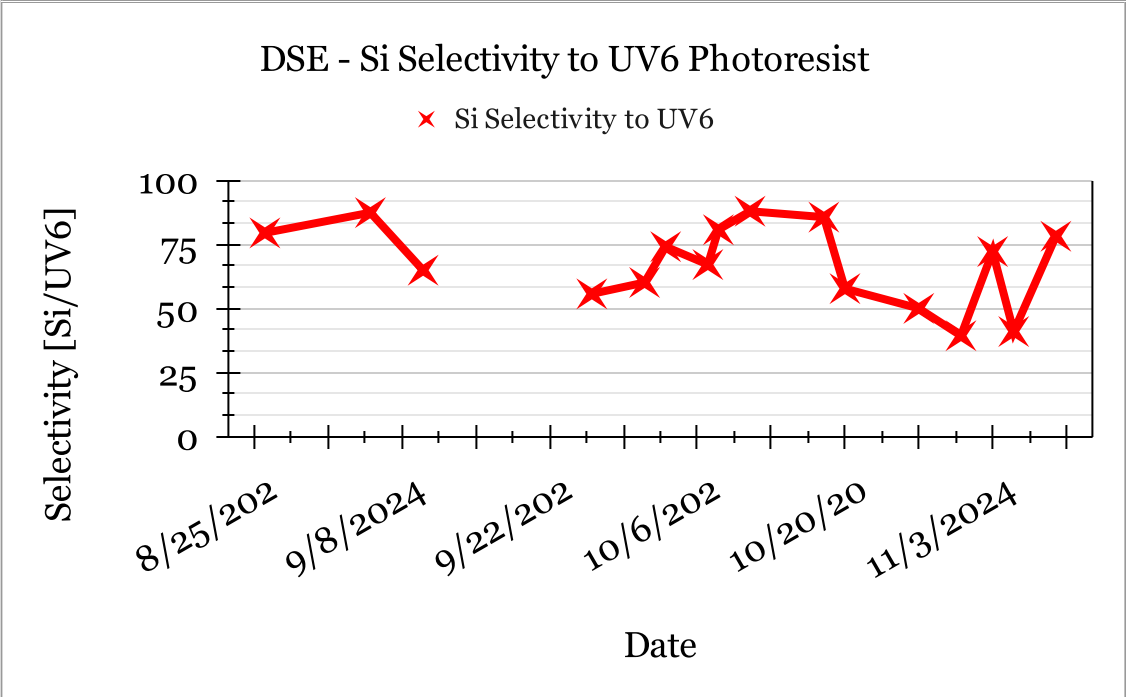
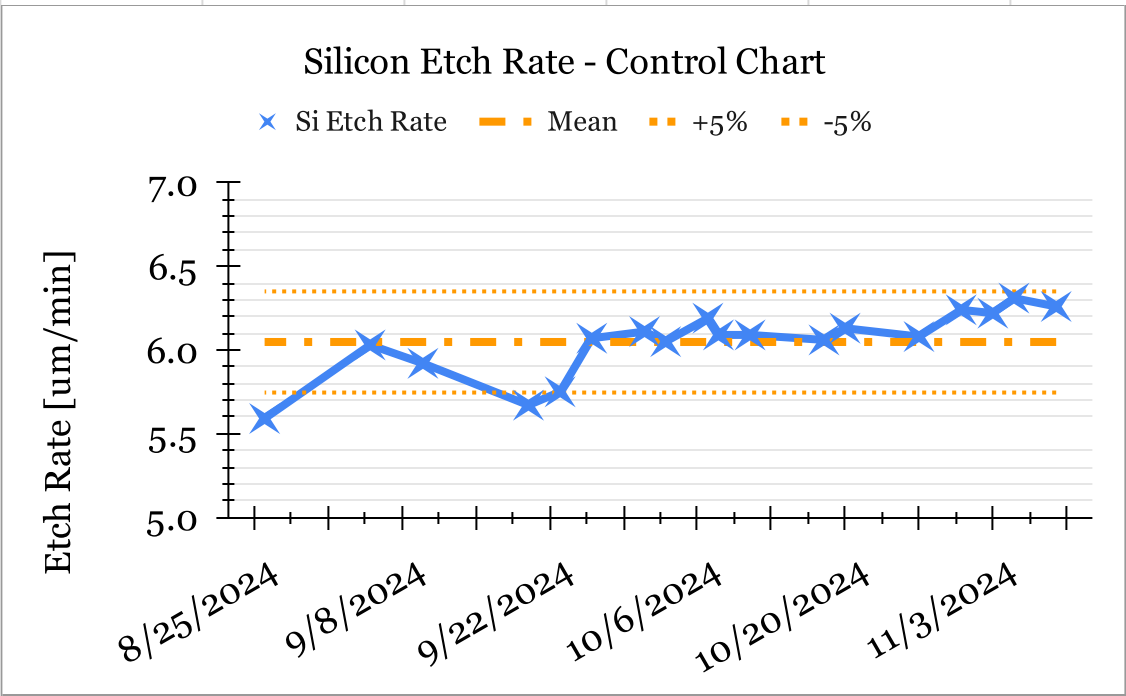


Dep - 25mTorr, C4F7/Ar=150/30sccm, LF Bias/ICP=11/2000W, 2s
 Etch A - 40mTorr, SF6/Ar=150/30sccm, LF Bias/ICP=200/2000W, 2s
 Etch B - 60mTorr, SF6/Ar=250/30sccm, LF Bias/ICP=11/2000W, 2s
 ~50% Open area on 4" wafer

65 cycles

Date (link to data)	Sample #	Center Dektak Etch Rate (um/min)	Center Selectivity (Si/UV6)	Observations/Notes	Link to SEMs	Cross Section SEM	Sidewall SEM
INSERT NEW DATA BELOW THIS ROW							
11/09/24	24109DSE-Si	6.26	78.21				
11/05/24	24105DSE-Si	6.31	41.02				
11/02/24	24103DSE-Si	6.22	72.23				
10/24/24	24103DSE-Si	6.24	39.41		SEM		
10/27/24	24102DSE-Si	6.08	50.06				
10/20/24	24102DSE-Si	6.13	57.77				
10/18/24	24108DSE-Si	6.06	85.67				
10/11/24	24101DSE-Si	6.09	87.98		SEMs		
10/08/24	241008DSE-Si	6.09	80.76				
10/07/24	241007DSE-Si	6.19	67.16		SEMs		
10/03/24	241003DSE-Si	6.05	74.15				
10/01/24	241001DSE-Si	6.11	60.17				
09/26/24	240926DSE-Si	6.07	55.73				
09/23/24	240923DSE-Si	5.75		Ashed using YES asher, did not record selectivity			
09/20/24	240920DSE-Si	5.67		one of first runs after DSE came back up with brand new process chamber wall			
09/10/24	240910DSE-Si	5.92	64.96				
09/05/24	240905DSE-Si	6.03	87.43				
08/26/24	240826DSE-Si	5.59	79.52	initial development run	8/26/24 SEMs		



Filter Data:		PECVD2: SIGN4 Recipe	Dep Recipe -->	SEASONING TIME: 600 seconds	MEAN VALS (for plotting)		SPC UPPER (for plotting)		SPC LOWER (for plotting)			
DATE	Sample #	ETCH RATE (nm/min)	ETCH SELECTIVITY (SiO2/PR)	ETCH RATE (nm/min)	ETCH SELECTIVITY (SiO2/PR)	ETCH RATE (nm/min)	ETCH SELECTIVITY (SiO2/PR)	ETCH RATE (nm/min)	ETCH SELECTIVITY (SiO2/PR)			
Days from today: 490		MEAN VALUES		6.048	67.6394	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
Start Date: 7/29/2023		SPC UPPER		6.350166667	71.02134375	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
SPC Cutoffs:		SPC LOWER		5.745	64.257	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
ETCH RATE (nm/min)	5	Date (link to data)		Sample #	th Rate (um/min)	lectivity (Si/UV6)	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625
ETCH SELECTIVITY (SiO2/PR)	5	11/9/2024	241109DSE-Si	6.260	78.2100	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		11/25/2024	241105DSE-Si	6.310	41.0200	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		11/26/2024	241103DSE-Si	6.220	72.2300	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/31/2024	241031DSE-Si	6.240	39.4100	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/27/2024	241027DSE-Si	6.080	50.0600	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/20/2024	241020DSE-Si	6.130	57.7700	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/18/2024	241018DSE-Si	6.060	85.6700	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/11/2024	241011DSE-Si	6.090	87.9800	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/8/2024	241008DSE-Si	6.090	80.7600	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/7/2024	241007DSE-Si	6.190	67.1600	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/3/2024	241003DSE-Si	6.060	74.1600	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		10/1/2024	241001DSE-Si	6.110	60.1700	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		9/25/2024	240925DSE-Si	6.070	55.7300	6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		9/23/2024	240923DSE-Si	5.750		6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		9/20/2024	240920DSE-Si	5.670		6.04777778	67.639375	6.350166667	71.02134375	5.745388889	64.25740625	
		9/10/2024	240910DSE-Si	5.920	64.9600							
		9/5/2024	240905DSE-Si	6.030	87.4300							
		8/26/2024	240826DSE-Si	5.590	79.5200							

